



BUK761R6-40E

N-channel TrenchMOS standard level FET

5 September 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404A package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

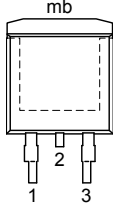
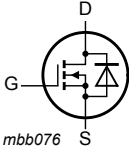
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	40	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 1	[1]	-	120	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ Fig. 2	-	-	349	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ Fig. 11	-	1.3	1.57	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 32\text{ V};$ Fig. 13; Fig. 14	-	48.2	-	nC

[1] Continuous current is limited by package.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>D2PAK (SOT404A)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK761R6-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK761R6-40E	BUK761R6-40E

8. Limiting values

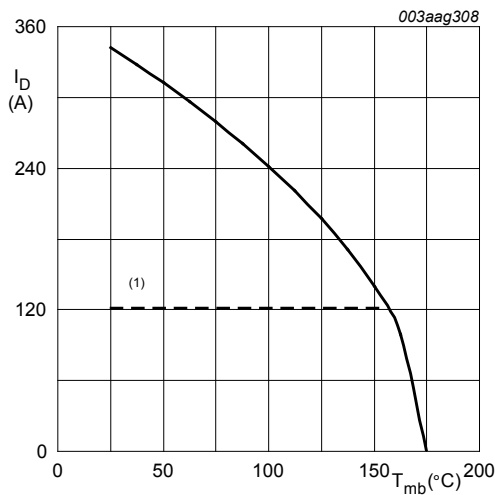
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	40	V
V_{GS}	gate-source voltage	$T_j \leq 175\text{ °C}$; DC	-20	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	[1]	120	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	[1]	120	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	1355	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2	-	349	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ }^\circ\text{C}$	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^\circ\text{C}$		-	1355	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120\text{ A}$; $V_{sup} \leq 40\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped; Fig. 3	[2][3]	-	1008	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



(1) Capped at 120A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

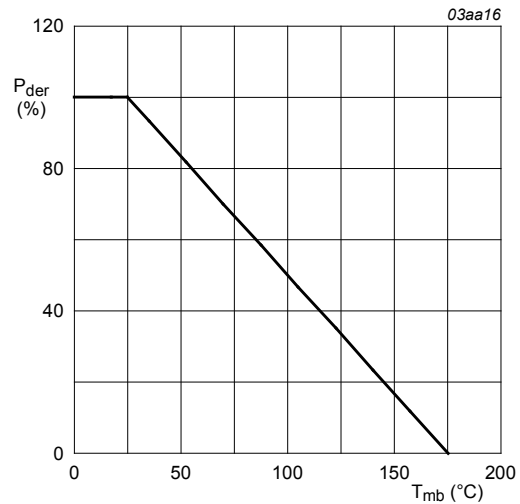


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

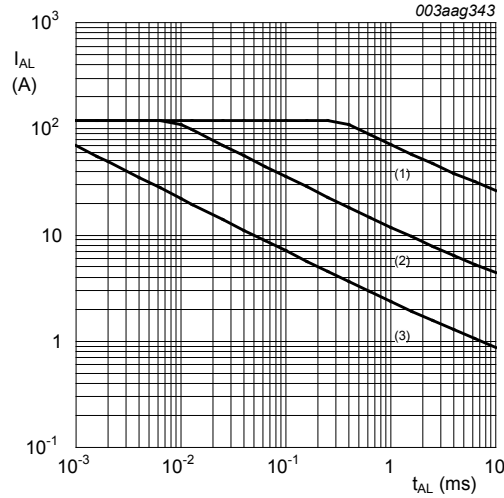


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^\circ C$; (2) $T_{j (init)} = 150^\circ C$; (3) Repetitive Avalanche

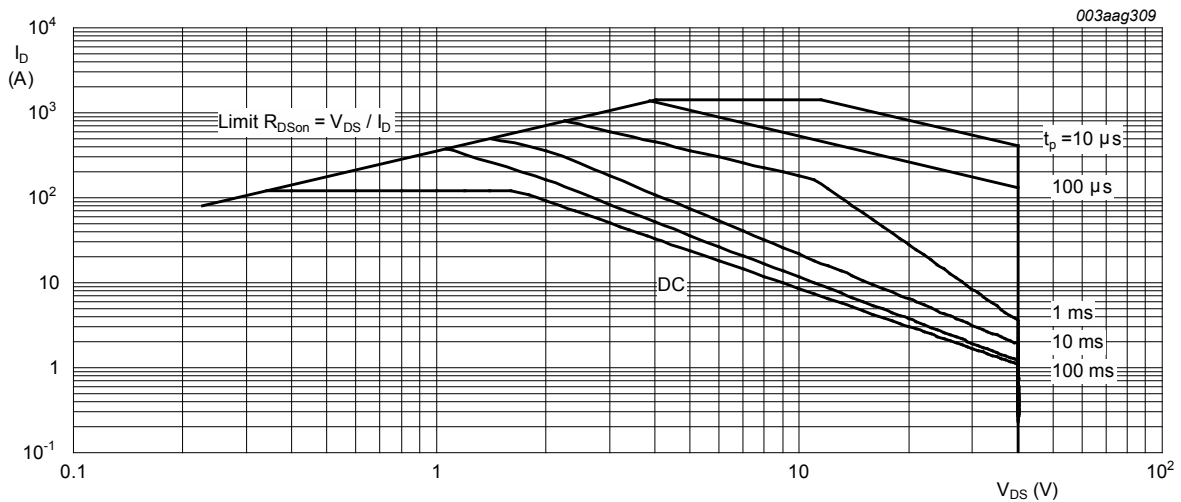


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^\circ C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

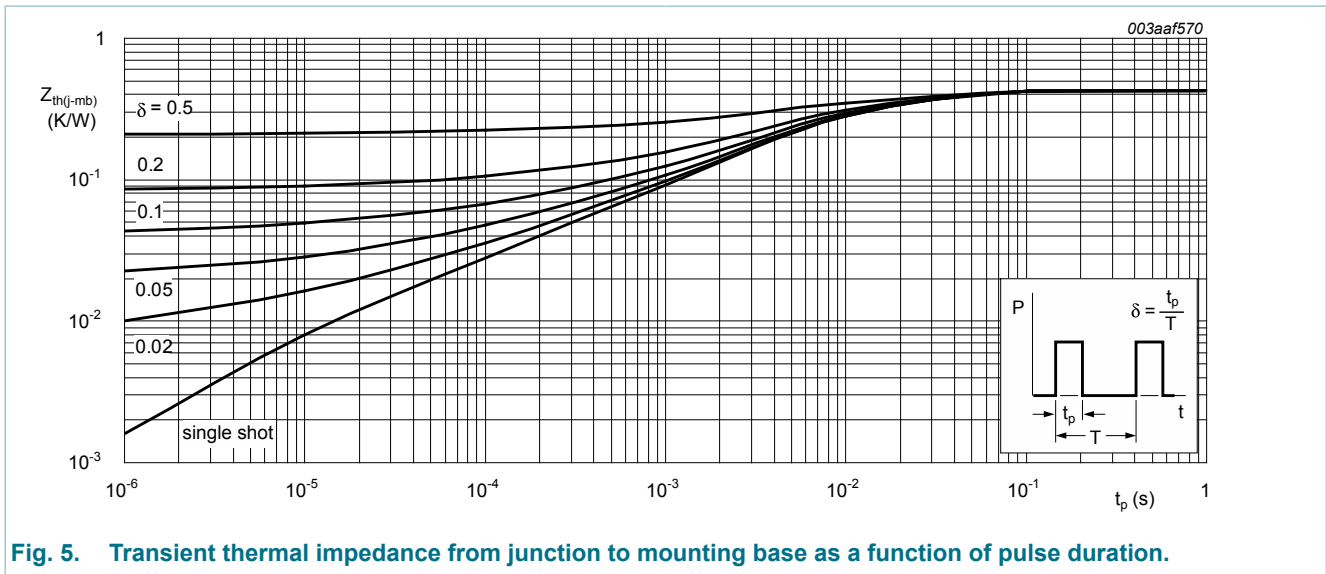


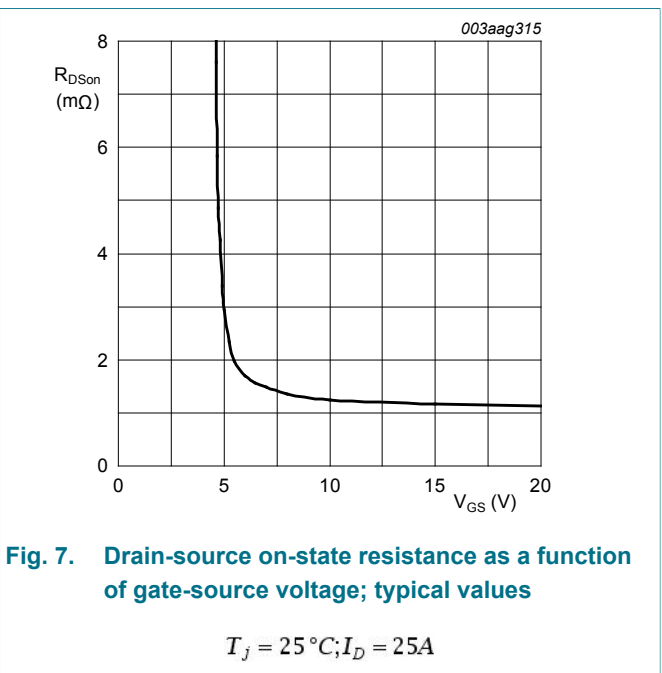
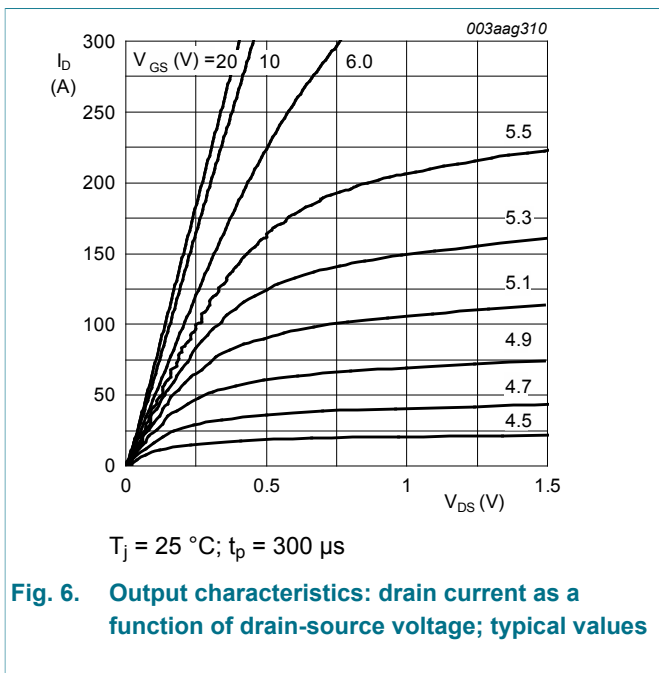
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$	40	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 \text{ }^\circ C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 25 \text{ }^\circ C;$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = -55 \text{ }^\circ C;$ Fig. 10	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 175 \text{ }^\circ C;$ Fig. 10	1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$	-	0.25	2	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 25 \text{ }^\circ C;$ Fig. 11	-	1.3	1.57	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 175 \text{ }^\circ C;$ Fig. 12; Fig. 11	-	-	3	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 13; Fig. 14	-	145	-	nC
Q_{GS}	gate-source charge		-	35.7	-	nC
Q_{GD}	gate-drain charge		-	48.2	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$	-	8500	11340	pF
C_{oss}	output capacitance	$T_j = 25\text{ }^\circ\text{C};$ Fig. 15	-	1620	1950	pF
C_{rss}	reverse transfer capacitance		-	985	1350	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.2\text{ }\Omega; V_{GS} = 10\text{ V};$	-	42	-	ns
t_r	rise time	$R_{G(ext)} = 5\text{ }\Omega$	-	60	-	ns
$t_{d(off)}$	turn-off delay time		-	121	-	ns
t_f	fall time		-	83	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	0.77	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	56	-	ns
Q_r	recovered charge	$V_{DS} = 25\text{ V}$	-	94	-	nC



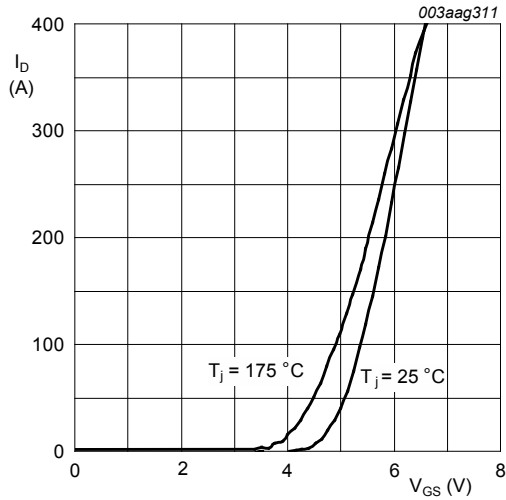


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 12 V$

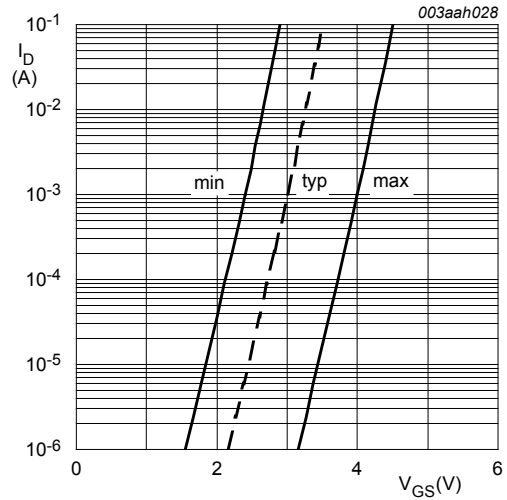


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25 °C; V_{DS} = 5 V$

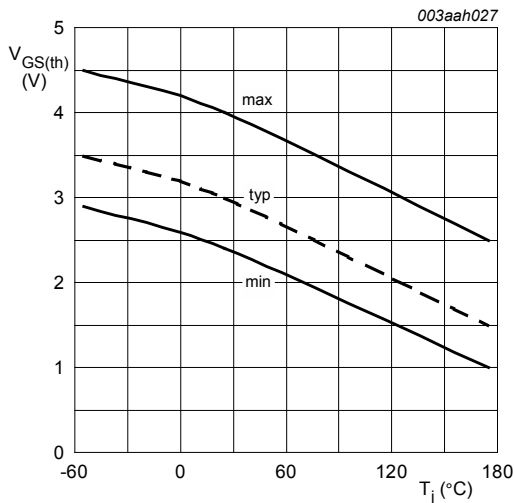


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 mA; V_{DS} = V_{GS}$

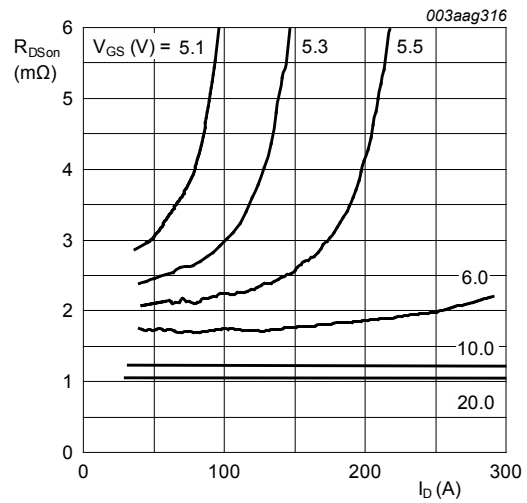


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25 °C; t_p = 300 \mu s$

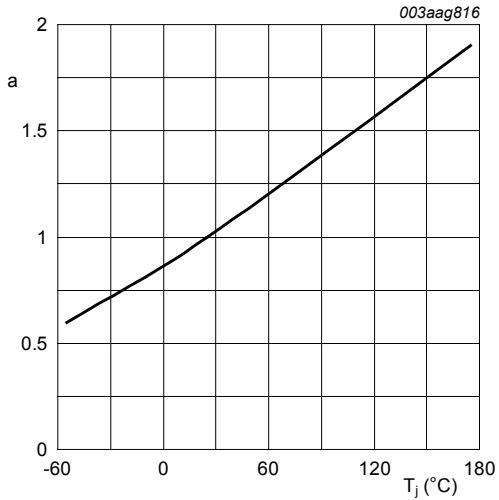
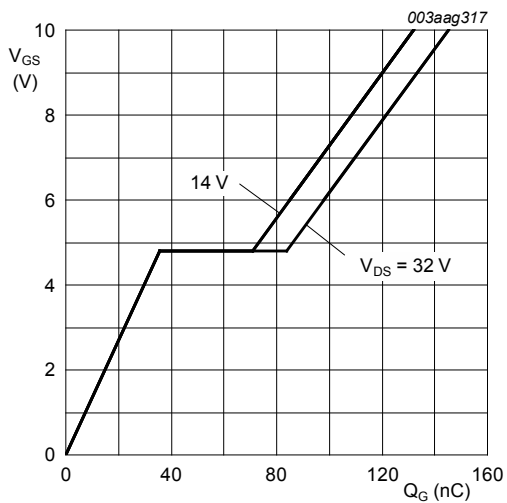


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25\text{ }^\circ\text{C})}}$$

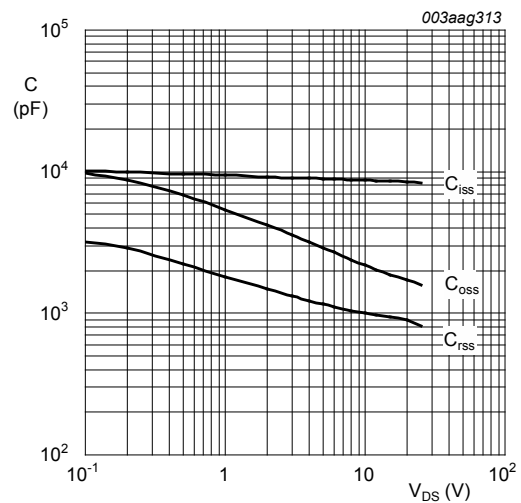


Fig. 13. Gate charge waveform definitions



$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

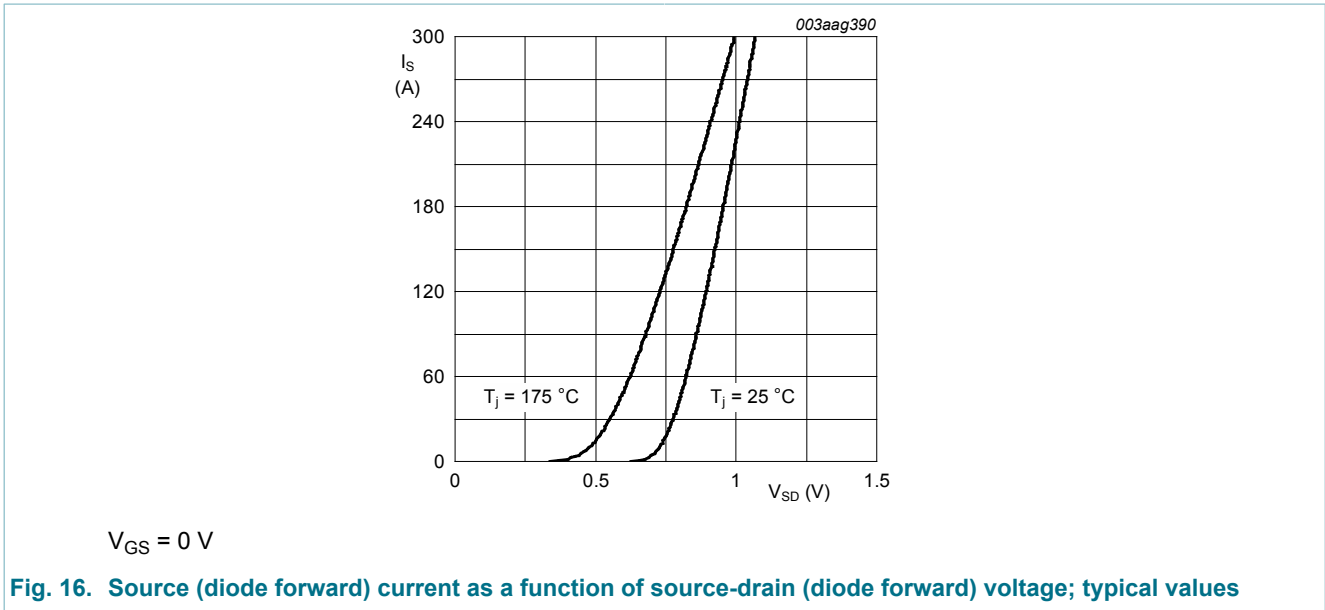
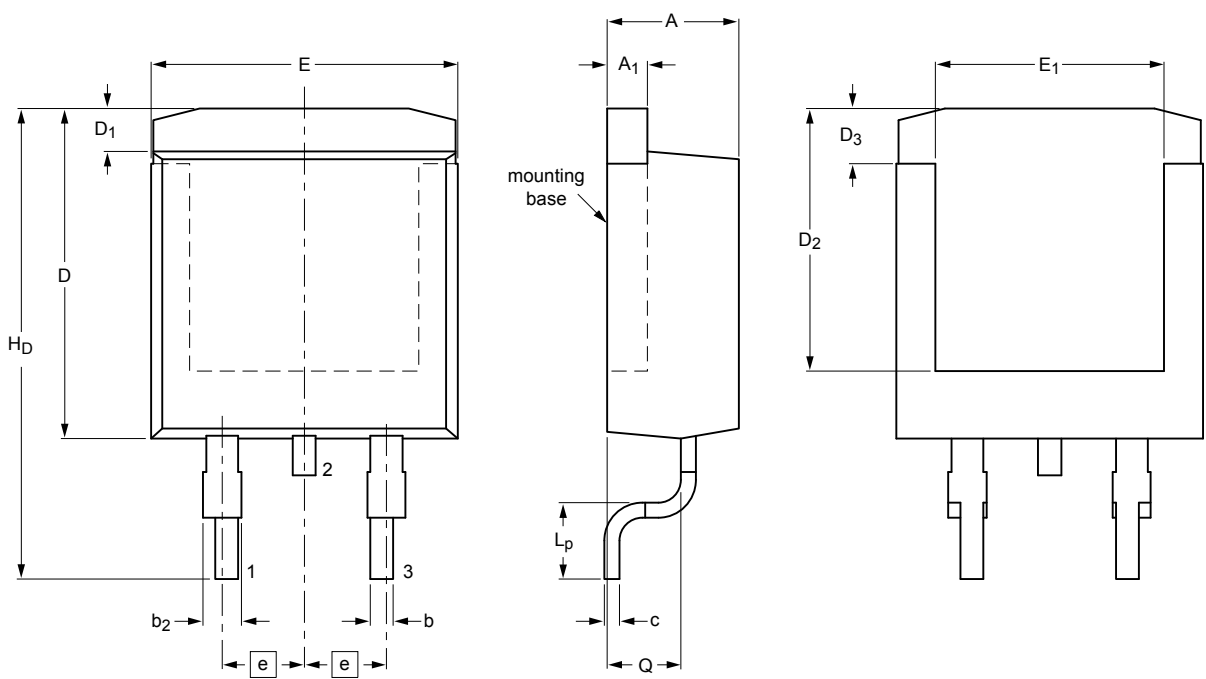


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) SOT404A



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₂	c	D _{max}	D ₁	D ₂	D ₃	E	E ₁	e	H _D	L _p	Q
max	4.5	1.40	0.85	1.45	0.64	11	1.6	8.6	1.85	10.3	8.1		15.8	2.9	2.6
nom												2.54			
min	4.1	1.27	0.60	1.05	0.46		1.2	8.0	1.40	9.7	7.6		14.8	2.1	2.2

sot404a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT404A						13-02-28 13-03-12

Fig. 17. Package outline D2PAK (SOT404A)

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 5 September 2013